

**12A 4Quadrants TRIACs**

**Product Summary**

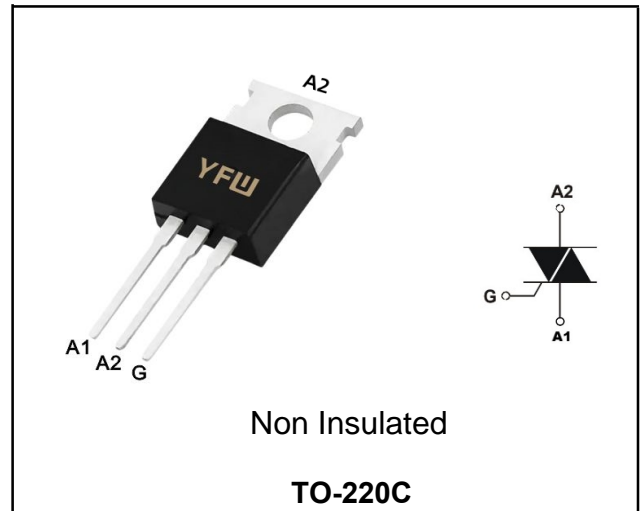
Symbol	Value	Unit
$I_{T(AV)}$	12	A
$V_{DRM} V_{RRM}$	600/800	V
$V_{TM}$	1.55	V

**Features**

With high ability to withstand the shock loading of arge current, Provide high dv/dt rate with strong resistance to electromagnetic interference

**Application**

Power charger, T-tools, massager, solid staterelay, AC Motor speed regulation and so on.



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit	
Repetitive peak off-state voltage	$V_{DRM}$	600/800	V	
Repetitive peak reverse voltage	$V_{RRM}$	600/800	V	
RMS on-state current	$I_{T(RMS)}$	12	A	
Non repetitive surge peak on-state current (full cycle, F=50Hz)	$I_{TSM}$	95	A	
$I^2t$ value for fusing (tp=10ms)	$I^2t$	45	A <sup>2</sup> s	
Critical rate of rise of on-state current ( $I_G = 2 \times I_{GT}$ )	$di/dt$	I - II - III	50	A/ $\mu$ s
		IV	10	
Peak gate current	$I_{GM}$	2	A	
Gate peak power	$I_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Junction Temperature	$T_J$	-40~+150	°C	
Storage Temperature	$T_{STG}$	-40 ~+125	°C	

**Electrical characteristics (TA=25°C, unless otherwise noted)**

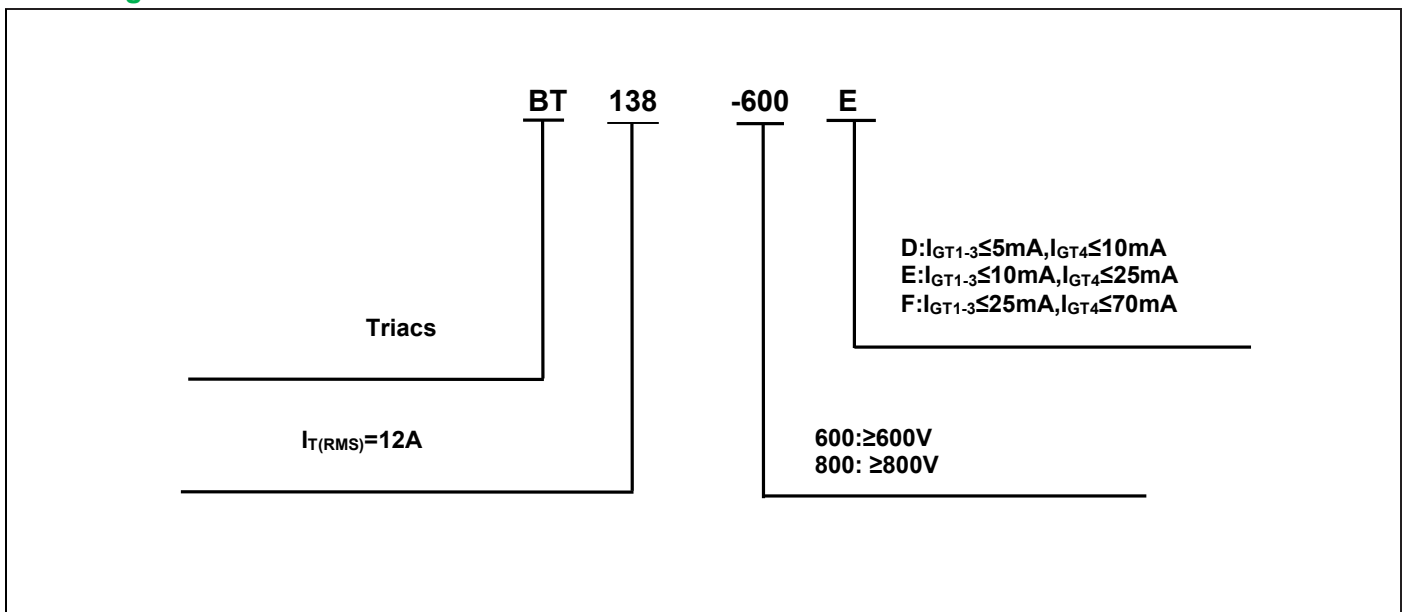
Parameter	Symbol	Test Condition	Value			Unit	
			D	E	F		
Gate trigger current	$I_{GT}$	$V_D=12V$ , $I_T=0.1A$ , $T_j=25^\circ C$ , Fig.6	I - II -III	$\leq 5$	$\leq 10$	$\leq 25$	<b>mA</b>
			IV	$\leq 10$	$\leq 25$	$\leq 70$	
Gate trigger voltage	$V_{GT}$		I - II -III-IV	$\leq 1.3$			<b>V</b>
Gate non-trigger voltage	$V_{GD}$	$V_D=V_{DRM}$ , $T_j=125^\circ C$	$\geq 0.2$			<b>V</b>	
Holding current	$I_H$	$V_D=12V$ , $I_{GT}=0.1A$ , $T_j=25^\circ C$ , Fig.6	I - II -III-IV	$\leq 10$	$\leq 30$	$\leq 30$	<b>mA</b>
Latching current	$I_L$		I -III-IV	$\leq 15$	$\leq 30$	$\leq 40$	<b>mA</b>
			II	$\leq 20$	$\leq 40$	$\leq 60$	<b>mA</b>
Critical-rate of rise of commutation voltage	$dV_D/dt$	$V_D=2/3V_{DRM}$ , $T_j=125^\circ C$	$\geq 10$	$\geq 20$	$\geq 50$	<b>V/us</b>	

**STATIC CHARACTERISTICS**

Forward "on" voltage	$V_{TM}$	$I_{TM}=15A$ , $t_p=380us$ , Fig.4	$\leq 1.55$			<b>V</b>	
Repetitive Peak Off-State Current	$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	$\leq 5$		$\leq 5$	<b>uA</b>
Repetitive Peak Reverse Current	$I_{RRM}$		$T_j=125^\circ C$	$\leq 0.5$		$\leq 0.5$	<b>mA</b>

**THERMAL RESISTANCES**

Thermal resistance	$R_{th(j-c)}$	Junction to case	TYP.	1.4	<b>°C/W</b>
	$R_{th(j-a)}$	Junction to ambient	TYP.	60	<b>°C/W</b>

**Ordering Information**


Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

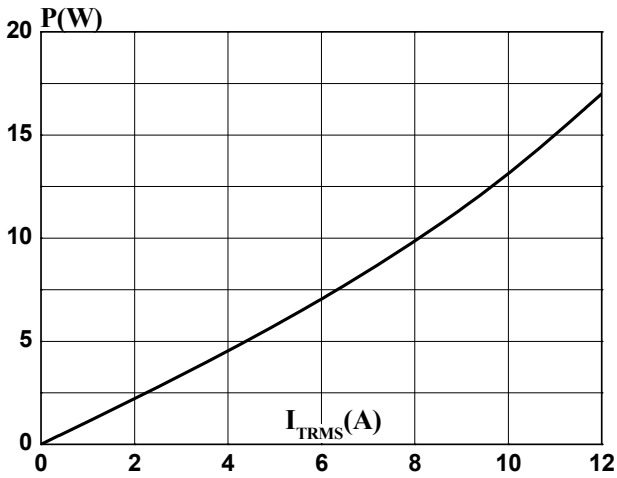


FIG.2: RMS on-state current versus case temperature (full cycle)

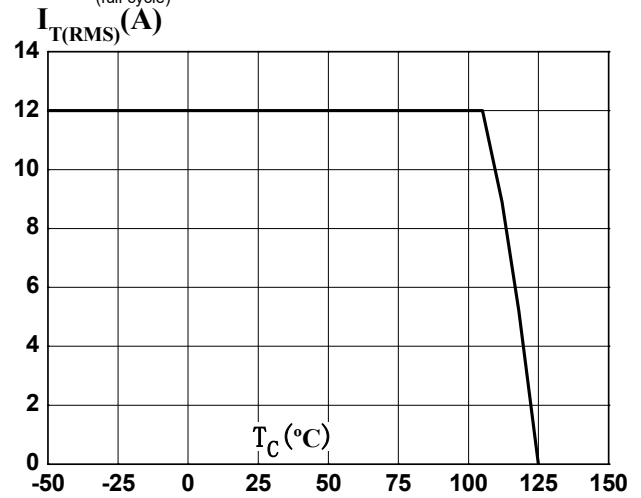


FIG.3: Surge peak on-state current versus number of cycles

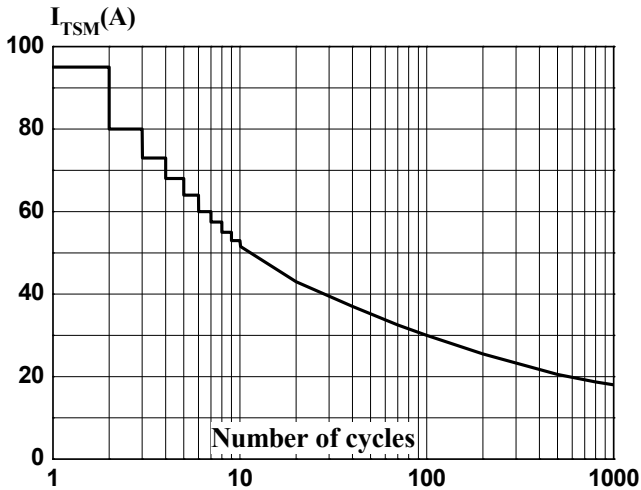


FIG.4: On-state characteristics (maximum values)

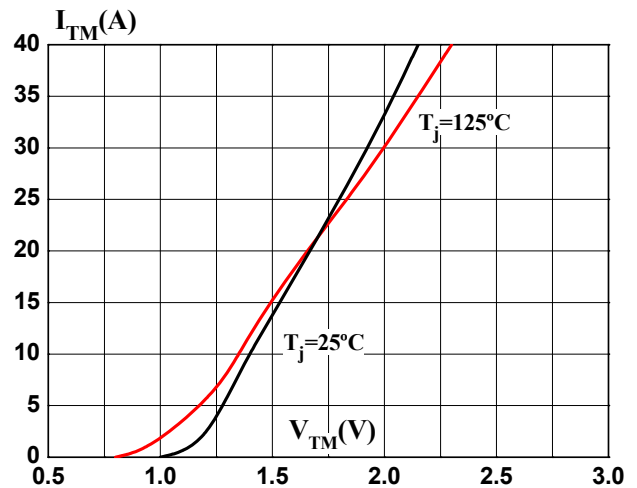


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$

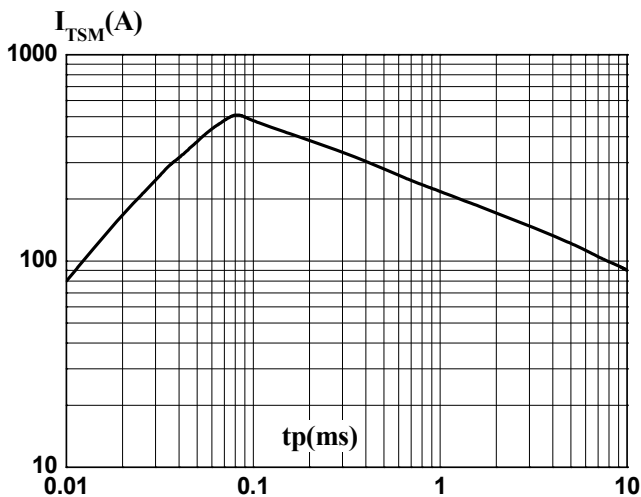
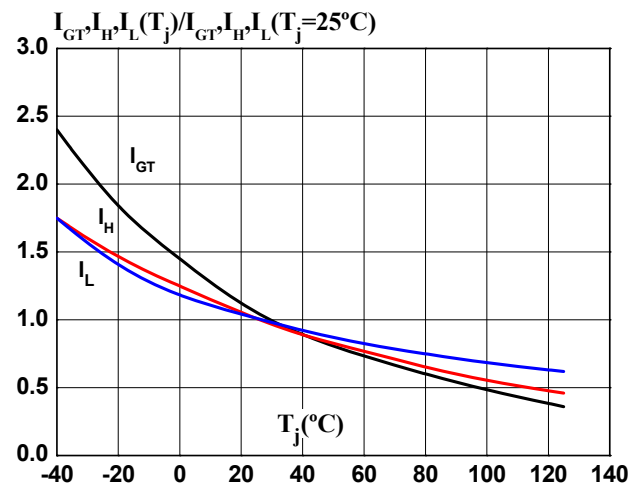
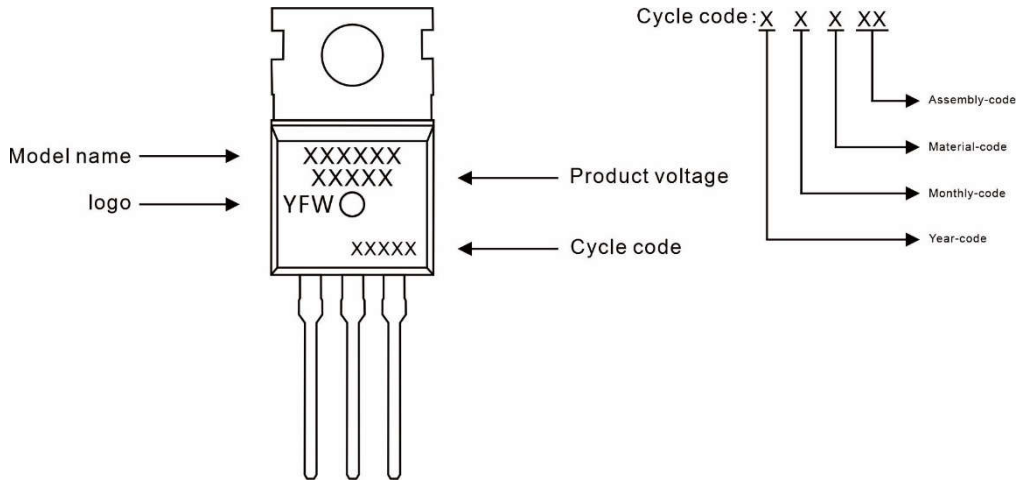


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



**Marking Diagram**



**Ordering information**

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
BT138	TO-220C	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

**Package Dimensions**

**TO-220C**

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	9.70	10.40	0.382	0.409
B	6.13	6.82	0.241	0.269
C	9.00	9.40	3.54	0.37
D	0.70	0.92	0.0276	0.0362
D1	1.18	1.45	0.047	0.057
D2	1.22	1.32	0.048	0.052
E	2.34	2.74	0.092	0.108
L	15.70	16.14	0.62	0.64
L1	9.60	10.60	0.38	0.42
L2	12.60	13.60	0.50	0.54
K	2.20	2.75	0.087	0.108
T	4.30	4.71	0.169	0.185
T1	1.20	1.42	0.0472	0.056
T2	0.38	0.65	0.015	0.026
ΦR	3.55	3.78	0.14	0.15

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